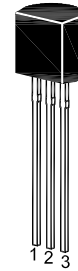


NPN Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into three groups, G, H and I, according to its DC current gain. As complementary type the PNP transistor 9012 is recommended.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 50\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 500\text{ mA}$	Current Gain Group G	h_{FE}	110	200	-
	H	h_{FE}	190	300	-
	I	h_{FE}	290	380	-
		h_{FE}	40	-	-
Collector Base Cutoff Current at $V_{CB} = 35\text{ V}$	I_{CBO}	-	100	nA	
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	100	nA	
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	40	-	V	
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	30	-	V	
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	V	
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	0.6	V	
Base Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{BE(sat)}$	-	1.2	V	
Base Emitter Voltage at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	V_{BE}	-	1	V	
Gain Bandwidth Product at $V_{CE} = 6\text{ V}$, $I_C = 20\text{ mA}$	f_T	100	-	MHz	



Fig. 1 P_{tot} - T_a

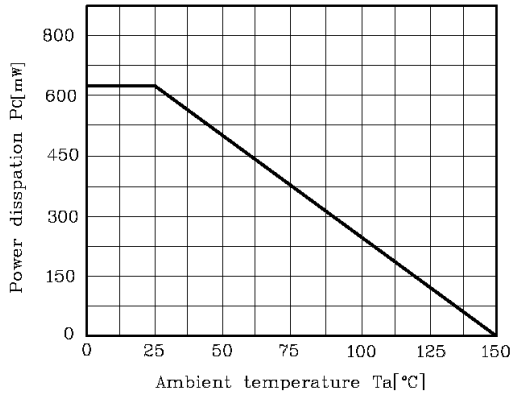


Fig. 2 I_C - V_{BE}

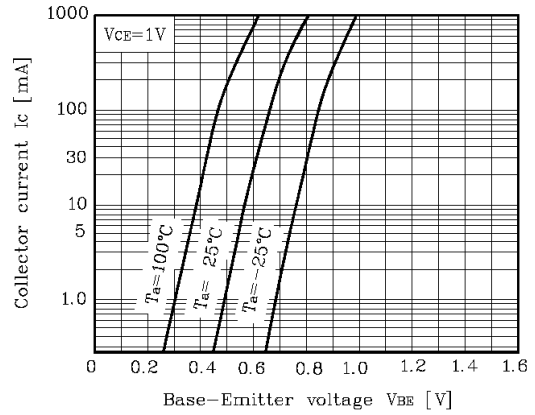


Fig. 3 I_C - V_{CE}

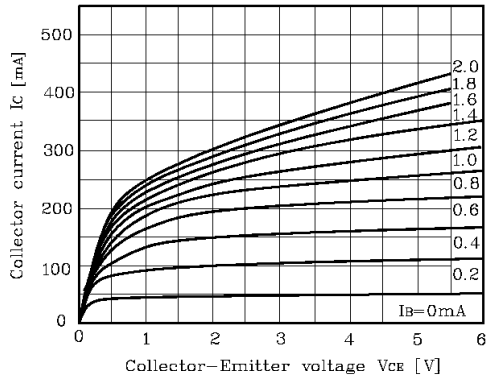


Fig. 4 $V_{CE(SAT)}$ - I_C

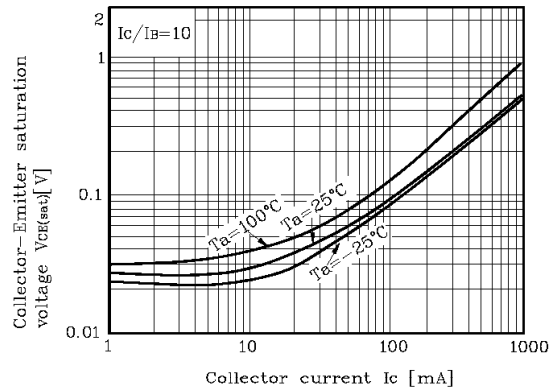


Fig. 5 h_{FE} - I_C

